

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE

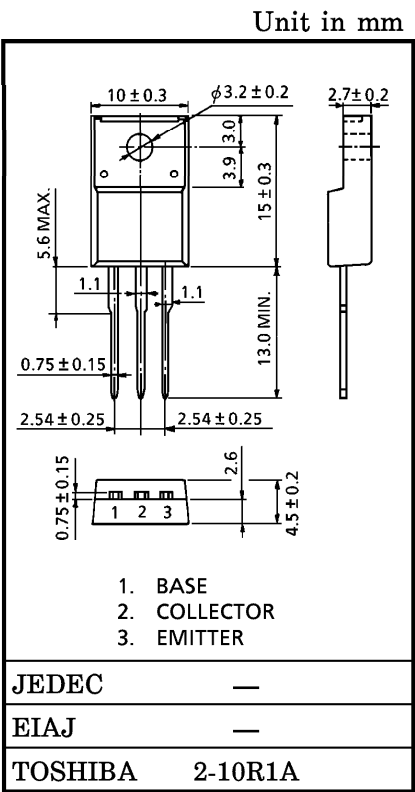
2SB1495

HIGH POWER SWITCHING APPLICATIONS

- High DC Current Gain
: $h_{FE}=2000$ (Min.) ($V_{CE}=-2V$, $I_C=-2A$)
- Low Saturation Voltage
: $V_{CE(sat)}=-1.5V$ (MAX.) ($I_C=-1.5A$)
- Complementary to 2SD2257

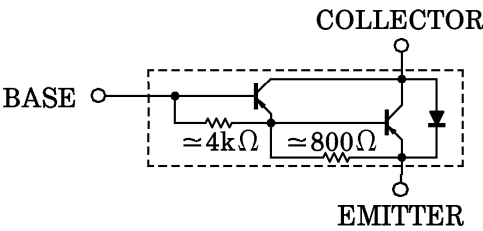
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CB0}	-100	V
Collector-Emitter Voltage		V_{CEO}	-100	V
Emitter-Base Voltage		V_{EB0}	-8	V
Collector Current	DC	I_C	-3	A
	Pulsed	I_{CP}	-5	
Base Current		I_B	-0.3	A
Collector Power Dissipation	Ta = 25°C	P_C	2.0	W
	Tc = 25°C		20	
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C

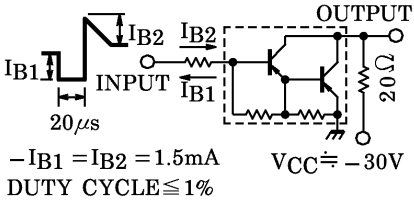


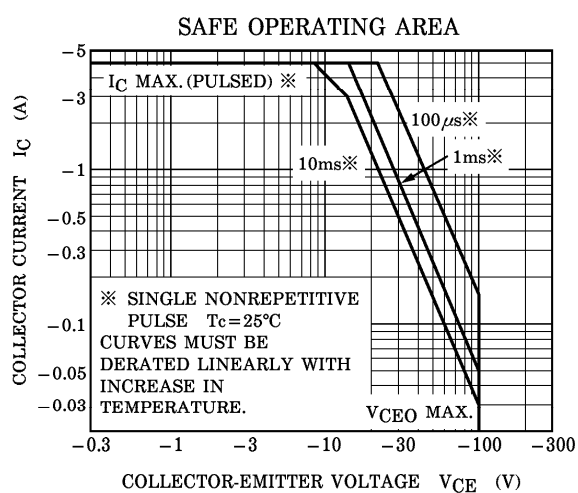
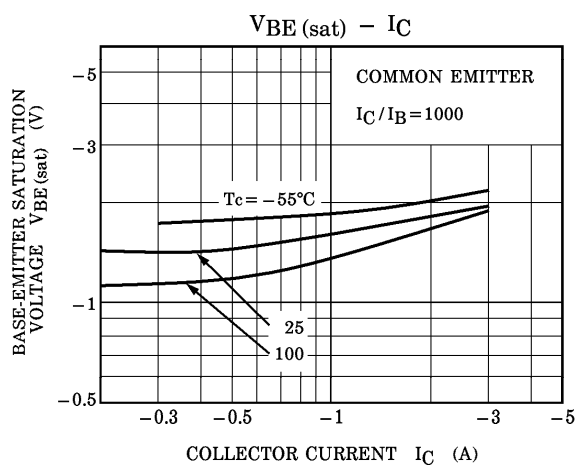
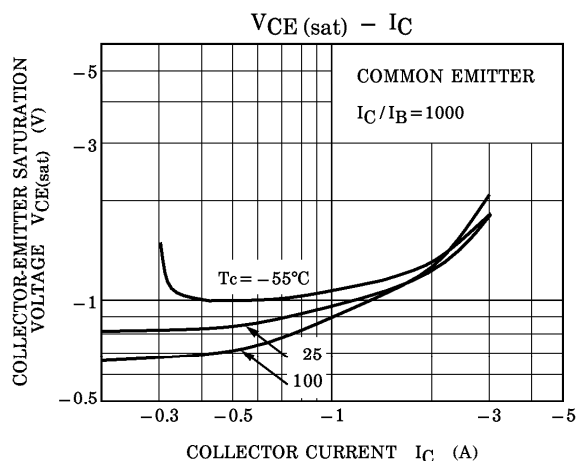
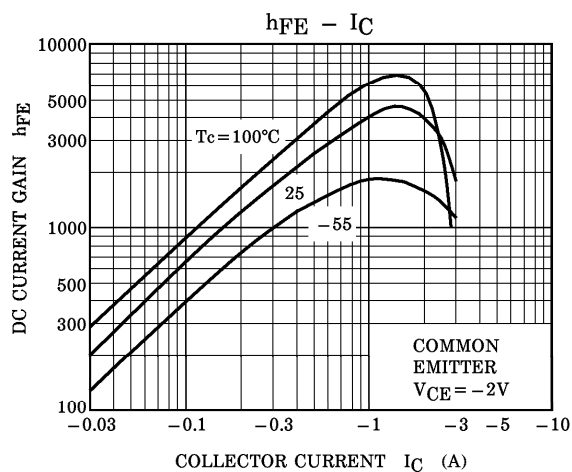
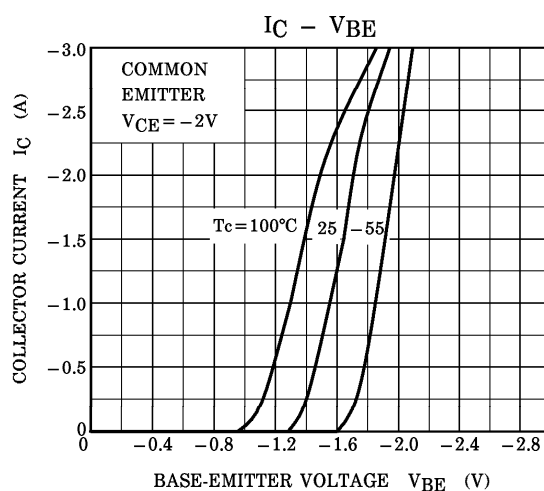
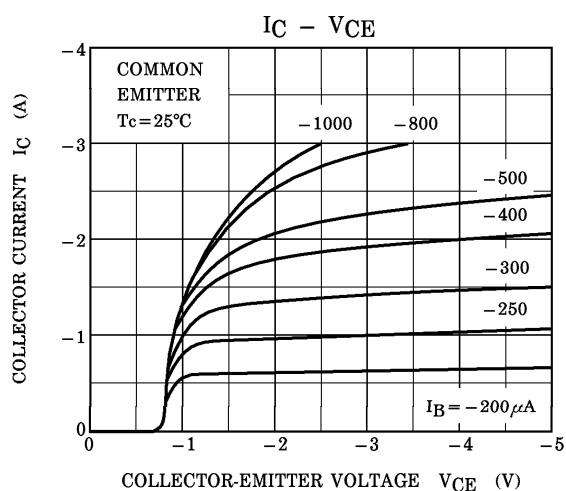
Weight : 1.7g

EQUIVALENT CIRCUIT



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = -100V, I_E = 0$	—	—	-10	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = -8V, I_C = 0$	-0.8	—	-4.0	mA
Collector-Emitter Breakdown Voltage		$V_{(BR) CEO}$	$I_C = -10mA, I_B = 0$	-100	—	—	V
DC Current Gain		$h_{FE(1)}$	$V_{CE} = -2V, I_C = -1A$	2000	—	—	
		$h_{FE(2)}$	$V_{CE} = -2V, I_C = -2A$	2000	—	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = -1.5A, I_B = -1.5mA$	—	—	-1.5	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C = -1.5A, I_B = -1.5mA$	—	—	-2.0	V
Switching Time	Turn-on Time	t_{on}	 <p> $-I_{B1} = I_{B2} = 1.5mA$ DUTY CYCLE $\leq 1\%$ $V_{CC} = -30V$ </p>	—	0.5	—	μs
	Storage Time	t_{stg}		—	1.0	—	
	Fall Time	t_f		—	0.4	—	



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